

Amendments to the Claims

A complete set of the existing claims are set forth below, with the amended claims showing deletions (bold double brackets) and insertions (underline).

1. – 18. (Cancelled)

19. (Currently amended) An apparatus, comprising:

a polishing pad platen adapted to hold and rotate a polishing pad;
a slurry arm extending at least a radial distance over the polishing pad platen,
the slurry arm adaptable to pivot over a pivoting axis, and having a nozzle adaptable to
deposit one or more slurry solutions onto the plishing pad~~including a first slurry port to~~
~~provide a first slurry solution~~; and

a control system coupled to the slurry arm to selectively position the slurry arm
over the polishing pad, said position based at least on a first anticipated location of a
substrate to be polished using the polishing pad at a first point in time.

20. (Previously presented) The apparatus of claim 19, wherein said control system to
selectively position the slurry arm over the polishing pad based on and in addition to the
first anticipated location of the substrate at the first point in time, a second anticipated
location of the substrate at a second point in time.

21. (Currently amended) The apparatus of claim 20, wherein said control system to
selectively control flow rate of ~~the~~a first slurry solution to be provided by ~~the~~a first slurry
port of the nozzle based on said first and second anticipated locations of the substrate
at the first and the second points in time, respectively.

22. (Previously presented) The apparatus of claim 20, wherein said control system to
selectively control rotation speed of the slurry arm based on said first and second
anticipated locations of the substrate at the first and the second points in time,
respectively.

23. (Currently amended) The apparatus of claim 19, wherein said first slurry port of the nozzle to provide a first slurry solution is aimed at a target area and the nozzle includes a second slurry port of the nozzle to provide a second slurry solution is aimed at the target area; and

wherein the control system to selectively control flow rates of the first and the second slurry solutions from each of the first and the second slurry ports at the first point in time in accordance with a selected polishing criteria.

24. (Previously presented) The apparatus of claim 23, wherein said first slurry solution is a chemical enhant and the second slurry solution is an abrasive slurry; and

wherein the control system to selectively control flow rates of the first and second slurry solutions to provide a predetermined concentration of the first and the second slurry solutions.

25. (Previously presented) The apparatus of claim 24, wherein the control system to reduce the flow rate of the second slurry solution at a later stage of the polishing of the substrate than at an earlier stage of the polishing of the substrate.

26. (Previously presented) The apparatus of claim 24, wherein the control system to increase the flow rate of the first slurry solution at a later stage of the polishing of the substrate than at an earlier stage of the polishing of the substrate.

27. (Currently amended) A method, comprising:

holding and rotating a polishing pad;

holding and rotating a substrate complementary to the rotating polishing pad;

extending a slurry arm at least a radial distance over the polishing pad, the slurry arm adapted to pivot over a pivoting axis, and having a nozzle adaptable to deposit one or more slurry solutions onto the plishing pad including a first slurry port to provide a first slurry solution; and

selectively positioning the slurry arm over the polishing pad, said positioning based at least on a first anticipated location of the substrate at a first point in time.

28. (Previously presented) The method of claim 27, wherein said selectively positioning is based on and in addition to the first anticipated location of the substrate at the first point in time, a second anticipated location of the substrate at a second point in time.

29. (Currently amended) The method of claim 28, further comprising selectively controlling flow rate of ~~the~~a first slurry solution to be provided by ~~the~~a first slurry port of ~~the nozzle~~ based on said first and second anticipated locations of the substrate at the first and the second points in time, respectively.

30. (Previously presented) The method of claim 28, further comprising selectively controlling rotation speed of the slurry arm based on said first and second anticipated locations of the substrate at the first and the second points in time, respectively.

31. (Currently amended) The method of claim 27, wherein ~~said~~a first slurry port of ~~the nozzle to provide a first slurry soution~~ is aimed at a target area and ~~the nozzle includes~~ a second slurry port of the nozzle to provide a second slurry solution is aimed at the target area; and

the method further comprising selectively controlling flow rates of the first and the second slurry solutions from each of the first and the second slurry ports at the first point in time in accordance with a selected polishing criteria.

32. (Previously presented) The method of claim 31, wherein said first slurry solution is a chemical enhant and the second slurry solution is an abrasive slurry; and

wherein said selectively controlling the flow rates of the first and the second slurry solutions comprises selectively controlling the flow of the first and the second

slurry solutions to provide a predetermined concentration of the first and the second slurry solutions.

33. (Previously presented) The method of claim 32, wherein said controlling the flow rates of the first and the second slurry solutions comprises reducing the flow rate of the second slurry solution at a later stage of the polishing of the substrate than at an earlier stage of the polishing of the substrate.

34. (Previously presented) The method of claim 32, wherein said controlling the flow rates of the first and the second slurry solutions comprises increasing the flow rate of the first slurry solution at a later stage of the polishing of the substrate than at an earlier stage of the polishing of the substrate.